

---

5. (Amended) A semiconductor wafer comprising:

a multi-layered insulation film formed on a surface of the wafer, said multi-layered insulation film comprising:

a first insulation layer comprising an organic material having a dielectric constant which is lower than a silicon oxide dielectric constant;

<sup>C2</sup> a second insulation layer comprising a polysiloxane compound having an Si-H group and formed on and adhering to a top of said first insulation layer;

a third insulation layer comprising an inorganic material and formed on and adhering to a top of said second insulation, and

a plurality of wires formed in said multi-layered insulation film, said multi-layered insulation film being disposed between said wires.

---

<sup>C3</sup> 36. (Amended) The semiconductor device according to claim 1, wherein said second insulation layer comprises methyl silsesquioxane.

---

41. (Amended) A semiconductor device having a damascene wiring structure, said semiconductor device comprising:

<sup>C4</sup> a multi-layered insulation film formed on a semiconductor substrate, said multi-layered insulation film having a plurality of recesses and comprising:

a first insulation layer comprising an organic material having a dielectric constant which is lower than a silicon oxide dielectric constant;

a second insulation layer comprising a polysiloxane compound having an Si-H

group and formed on and adhering to a top of said first insulation layer;

a third insulation layer comprising an inorganic material and formed on and adhering to a top of said second insulation layer; and

an electroconductive film formed in each recess in said plurality of recesses,

said multi-layered insulation film being disposed between each recess having said electroconductive film.

42. (Amended) A semiconductor device comprising a multi-layered insulation film and a plurality of wires formed on a semiconductor substrate said multi-layered insulation film comprising:

a first insulation layer comprising an organic material having a dielectric constant which is lower than a silicon dioxide dielectric constant;

a second insulation, adhesive layer comprising a polysiloxane compound having an Si-H group and formed on and being in contact with a top of said first insulation layer; and

a third insulation layer comprising an inorganic material and formed on and being in contact with a top of said second insulation, adhesive layer,

wherein said multi-layered insulation film is disposed between said wires in said plurality of wires.

---

#### **REMARKS**

Claims 1-8 and 31-42 are all the claims presently being examined in this application.

Claims 35 and 36 stand rejected upon informalities under 35 U.S.C. § 112, first and second paragraphs. Claims 1, 3-5, 7, 8, 34, 35, 37, 41 and 42 stand rejected under 35 U.S.C.